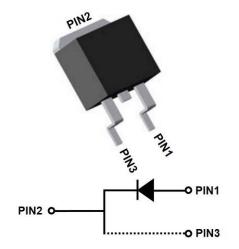
YJD106550BYG5

Silicon Carbide Schottky Diode

V _{RRM}	650V
I _{F (115°C)}	50A
Q _c	136nC



Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

- Package: TO-263
- Terminals: Tin plated leads
- Polarity: As marked

■Maximum Ratings (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Device marking code			D106550BYG5
Reverse voltage (Repetitive peak) @ T _j =25°C	V _{RRM}	V	650
Reverse voltage (Surge peak) @ T _j =25°C	V _{RSM}	V	650
Reverse voltage (DC) @ T _j =25°C	V _{DC}	V	650
Continuous forward current @ $T_c=25^{\circ}C$		A	86
Continuous forward current @ T _c =115°C	I _F		50
Continuous forward current @ T _c =135°C			39
Non-repetitive peak forward surge current @ T_c =25°C, tp=10ms, Half Sine Wave	I _{FSM}	А	380
Power Dissipation@ T _c =25°C	P	w	250
Power Dissipation@ T _c =110°C	P _{TOT}		108
i²t Value@ T _c =25°C ,tp=10ms	∫ i²dt	A ² S	722
Operating junction and Storage temperature range	T _j ,T _{stg}	°C	-55 to +175

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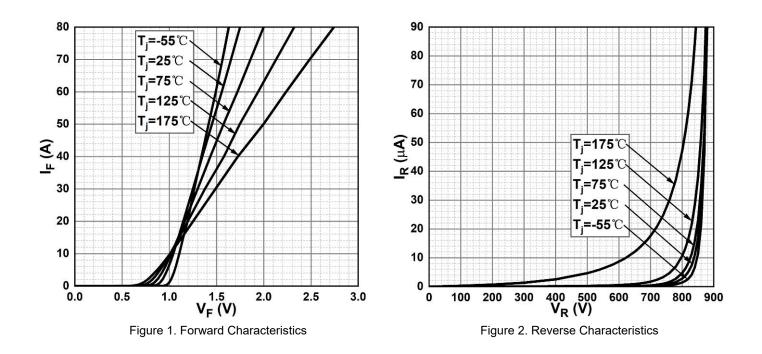
■Electrical Characteristics (Ta=25°C Unless otherwise specified)

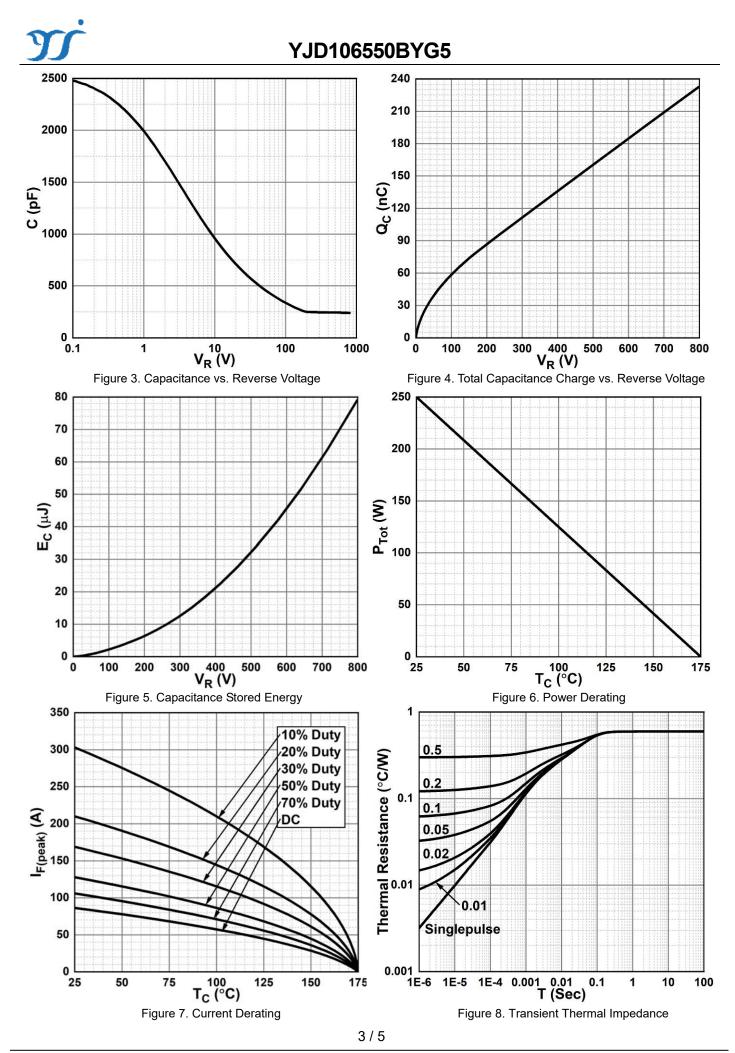
PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.		
E		V	I _F =50A, T _j =25°C	1.45	1.70		
Forward voltage	V _F		I⊧=50A, Tj=175°C	2.0	-		
Deveree eurrent			V _R =650V, T _j =25°C	1	25		
Reverse current I _R	I _R	μA	V _R =650V, T _j =175°C	20	-		
Total capacitive charge	Qc	nC	V_R =400V, T _j =25°C , QC= $\int_0 V^R C(V) dV$	136	-		
	al capacitance C pF				V _R =0V, f=1MHZ	2530	-
Total capacitance		pF	V _R =200V, f=1MHZ	250	-		
		V _R =400V, f=1MHZ	245	-			
Capacitance stored energy	Ec	μJ	V _R =400V	21	-		

■Thermal Characteristics (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Thermal resistance	$R_{_{ ext{ hetaJ-C}}}$	°C /W	0.60

■Typical Characteristics (Typical)

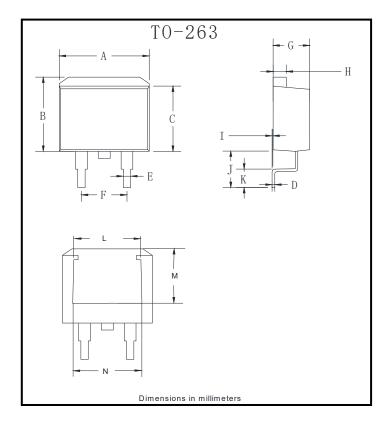




Yangzhou Yangjie Electronic Technology Co., Ltd.



Outline Dimensions



TO-263				
Dim	Min	Max		
А	9.5	11.5		
В	9.7	10.5		
С	8.4	9.0		
D	0.28	0.64		
E	0.68	0.94		
F	4.55	5.6		
G	4.04	5.10		
Н	1.14	1.4		
I	0	0.2		
J	4.9	6.05		
K	1.79	2.79		
L	7.3	7.9		
М	6.2	6.8		
N	7.6	8.2		

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Disclaimer

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